**Product data sheet** 

## 1. General description

EEPP<sup>™</sup>- Efficiency Enhanced Pt Planar diode in a 2-leads TO220-2L plastic package.

### 2. Features and benefits

- Fast switching
- Reduces switching losses with improved lower reverse recovery charge
- · Soft recovery characteristics
- Low thermal resistance
- Low leakage current
- High operating temperature capability (T<sub>i (max)</sub> = 175°C)
- Higher I<sub>FSM</sub> capability
- Planar termination structure

# 3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- · Uninterrupted Power Supply

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage		1200			V	
I <sub>F(AV)</sub>	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 85$ °C; Fig. 1; Fig. 2; Fig. 3	30		А		
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le 85$ °C; square-wave pulse		6	60		А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	270		А		
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		3	00		А
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.7	3.5	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	2.1	-	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	65	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	70	-	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	153	-	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$		-	173	-	ns
Avalanch	ne energy						
E <sub>AS</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C	3	30	-	-	mJ

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	V 14 A
2	Α	anode	7	K <del>    </del> A 001aaa020
mb	mb	mounting base; connected to cathod	O	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC30-1200P	TO220-2L	BYC30-1200PQ	Tube	50	SOD59	27-Nov-2012

# 7. Marking

### Table 4. Marking codes

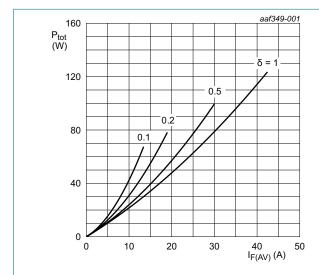
Type number	Marking codes
BYC30-1200P	BYC30-1200P

# 8. Limiting values

### Table 5. Limiting values

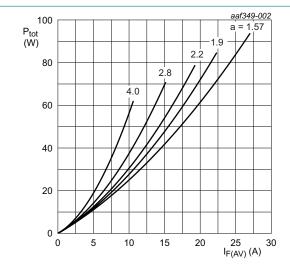
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		1200	V
$V_{\text{RWM}}$	crest working reverse voltage		1200	V
V <sub>R</sub>	reverse voltage	DC	1200	V
I <sub>F(AV)</sub>	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 85$ °C; Fig. 1; Fig. 2; Fig. 3	30	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 85 °C; square-wave pulse	60	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	270	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	300	Α
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.932 \text{ V; } R_{\text{s}} = 0.0231 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$ V<sub>o</sub> = 1.932 V; R<sub>s</sub> = 0.0231  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

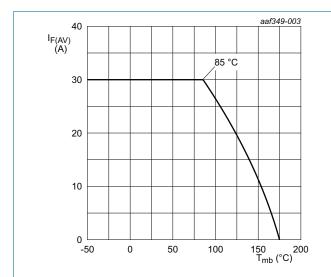


Fig. 3. Forward current as a function of mounting base temperature; maximum values

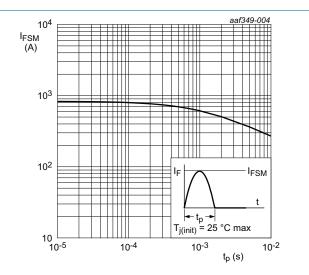


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	0.9	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

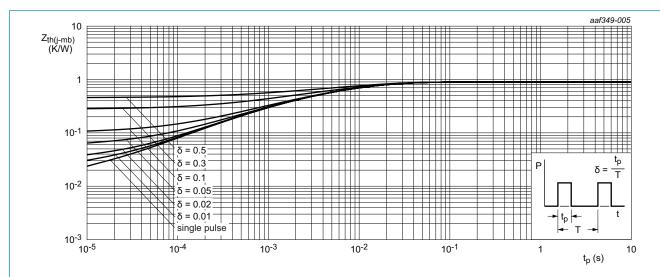


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

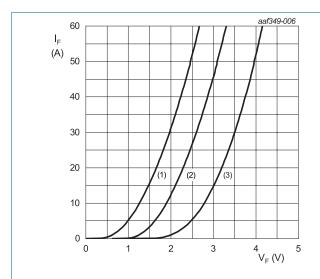
# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static ch	aracteristics						
$V_{F}$	forward current	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.7	3.5	V	
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	2.1	-	V	
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C	-	-	250	μA	
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 150 °C	-	-	1	mA	
Dynamic	characteristics						
Q <sub>r</sub>	reverse charge	$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	572	-	nC	
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	1573	-	nC	
			$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	1940	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	65	ns	
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	70	-	ns	
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	153	-	ns	
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	173	-	ns	
I <sub>RM</sub>	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	16	-	А	
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	21	-	А	
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	22	-	А	
Avalanch	ne energy		·				
E <sub>AS</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C	30	-	-	mJ	

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Hyperfast power diode



 $V_o$  = 1.932 V;  $R_s$  = 0.0231  $\Omega$ 

(1)  $T_j = 150 \, ^{\circ}\text{C}$ ; typical values

(2) T<sub>i</sub> = 150 °C; maximum values

(3)  $T_j = 25$  °C; maximum values



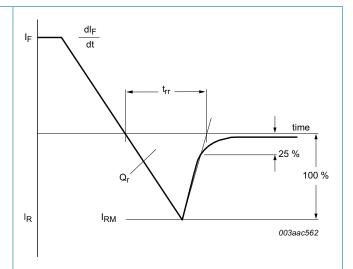
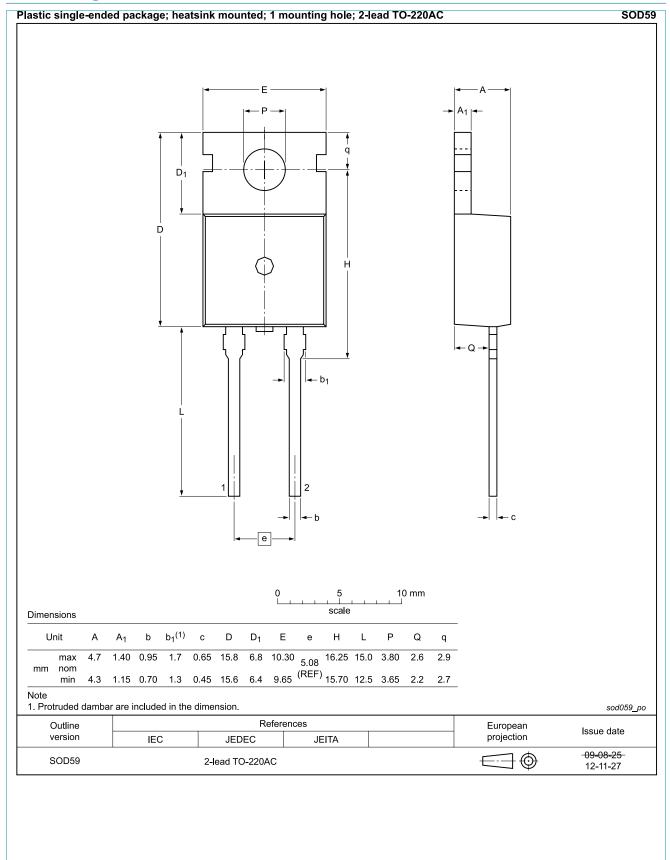


Fig. 7. Reverse recovery definitions; ramp recovery

# 11. Package outline



## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BYC30-1200P

Hyperfast power diode

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